



#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> Max	Ι <sub>D</sub> T <sub>A</sub> = +25°C
-60V	55mΩ @ V <sub>GS</sub> = -10V	-4.8A

#### Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for highefficiency power management applications.

#### Applications

- Disconnect Switches
- Motor Drive

#### Features

- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Low Profile SOIC Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

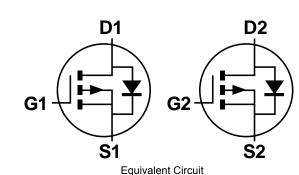
#### **Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208 <sup>(23)</sup>
- Weight: 0.074 grams (Approximate)



Top View

**SO-8** 



#### Ordering Information (Notes 4 & 5)

Product	Compliance	Case	Quantity per reel
ZXMP6A18DN8TA	Standard	SO-8	500
ZXMP6A18DN8TC	Standard	SO-8	2,500
ZXMP6A18DN8QTC	Automotive	SO-8	2,500

🗆 D1

□ D1

 $\Box D2$ 

 $\Box$  D2

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

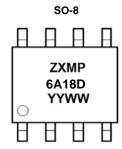
 See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_compliance\_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



ZXMP6A18D = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 11 = 2011) WW = Week (01 - 53)



### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	-60	V
Gate-Source Voltage		V <sub>GS</sub>	±20	V
	(Notes 7 & 9)		-4.8	
Continuous Drain Current (V <sub>GS</sub> = 10V)	T <sub>A</sub> = +70°C (Notes 7 & 9)	I <sub>D</sub>	-3.8	А
	(Notes 6 & 9)		-3.7	
Pulsed Drain Current	(Notes 8)	I <sub>DM</sub>	-23	А
Continuous Source Current (Body Diode)	(Notes 7)	ls	-3.3	A
Pulsed Source Current (Body Diode)	(Notes 8)	I <sub>SM</sub>	-23	A
Single Pulsed Avalanche Energy (L = 0.1mH)	(Note 11)	E <sub>AS</sub>	38.2	mJ
Single Pulsed Avalanche Current (L = 0.1mH)	(Note 11)	I <sub>AS</sub>	27.6	A

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Notes 6 & 9)		1.25 10		
Power Dissipation Linear Derating Factor	(Notes 6 & 10)	PD	1.8 14	W mW/°C	
	(Notes 7 & 9)		2.1 17		
	(Notes 6 & 9)		+100		
Thermal Resistance, Junction to Ambient	(Notes 7 & 10)	R <sub>0JA</sub>	+69	°C/W	
	(Notes 7 & 9)		+58		
Operating and Storage Temperature Range		TJ, T <sub>STG</sub>	-55 to +150	°C	

6. For a dual device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 1oz copper in still air conditions.

7. For a dual device surface mounted FR4 PCB measured at  $t \leq$  10 sec.

8. Repetitive rating 25mm x 25mm x 1.6mm FR4 PCB, D = 0.02, pulse width = 300 µs - pulse width limited by maximum junction temperature.

9. For a dual device with one active die.

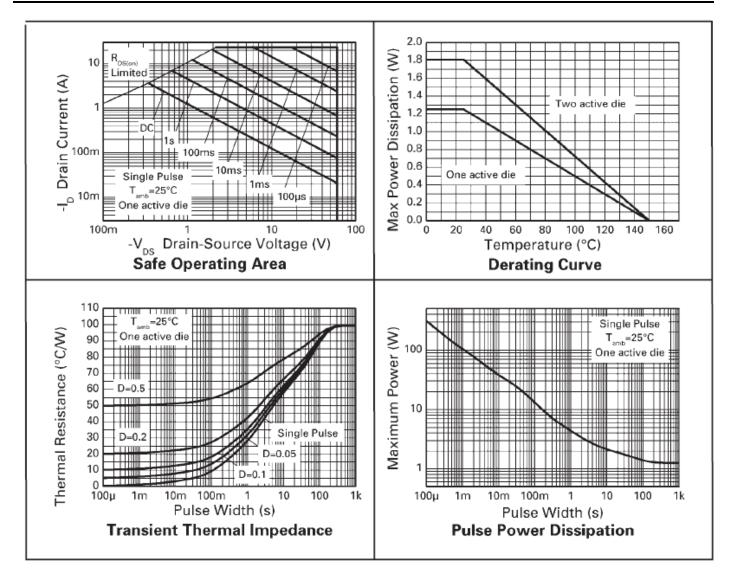
Notes:

10. For a device with two active die running at equal power.

11. IAR and EAR rating are based on low frequency and duty cycles to keep  $T_{\rm J}$  = +25°C.



## **Thermal Characteristics**





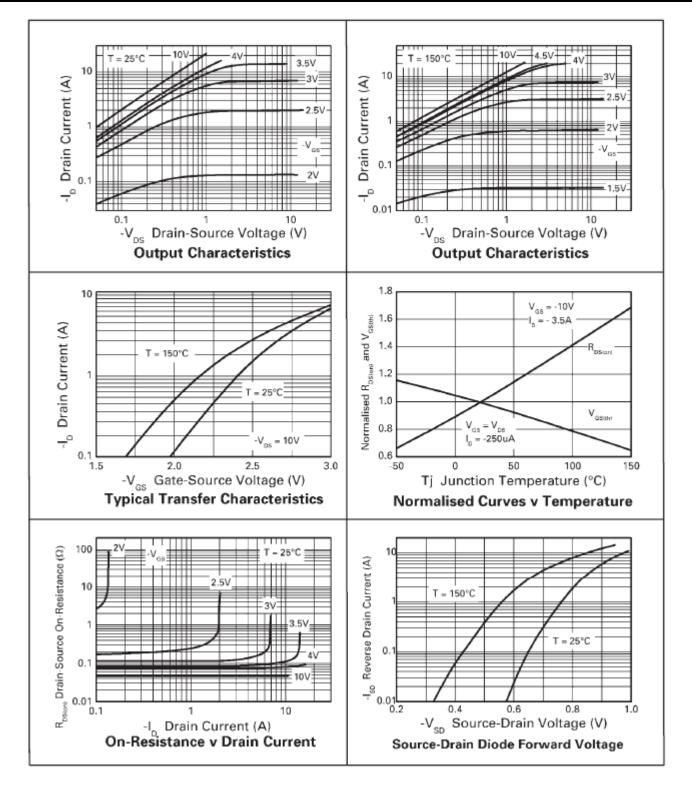
# Electrical Characteristics (@T<sub>A</sub>= +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Con	dition
OFF CHARACTERISTICS			•	•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	_	_	V	I <sub>D</sub> = -250µA, V <sub>GS</sub> = 0V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1	μA	$V_{DS} = -60V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_		±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V	
ON CHARACTERISTICS							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1	—	—	V	I <sub>D</sub> = -250µA, V <sub>DS</sub> = V <sub>0</sub>	GS
Statia Drain Source On Registence (Note 12)	Б			0.055	Ω	V <sub>GS</sub> = -10V, I <sub>D</sub> = -3.5/	٩
Static Drain-Source On-Resistance (Note 12)	R <sub>DS(ON)</sub>	_		0.08	12	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2.9	A
Forward Transconductance (Notes 12 & 14)	<b>g</b> fs	_	8.7	_	S	V <sub>DS</sub> = -15V, I <sub>D</sub> = -3.5/	۹.
Diode Forward Voltage (Note 12)	V <sub>SD</sub>	_	-0.85	-0.95	V	I <sub>S</sub> = -4.2A, V <sub>GS</sub> = 0V, T <sub>J</sub> = +25°C	
Reverse Recovery Time (Note 14)	t <sub>rr</sub>		37	_	ns	-I <sub>F</sub> = -2.1A, di/dt = 100A/μs, T <sub>J</sub> = +25°C	
Reverse Recovery Charge (Note 14)	Qrr	_	56		nC		
DYNAMIC CHARACTERISTICS (Note 14)							
Input Capacitance	Ciss		1580	—	pF	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V -f = 1MHz	
Output Capacitance	Coss		160	—	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>		140	—	pF		
Total Gate Charge (Note 13)	Qg	_	23	—	nC	V <sub>GS</sub> = -5V	
Total Gate Charge (Note 13)	Qg	_	44	—	nC	$V_{GS} = -10V$ $V_{DS} = -30V$ $I_{D} = -3.5A$	
Gate-Source Charge (Note 13)	Q <sub>gs</sub>	_	3.9	_	nC		
Gate-Drain Charge (Note 13)	Q <sub>gd</sub>	_	9.8	_	nC		
Turn-On Delay Time (Note 13)	t <sub>D(on)</sub>	_	4.6	_	ns	V <sub>DD</sub> = -30V, V <sub>GS</sub> = -10V I <sub>D</sub> = -1A, R <sub>G</sub> ≅ 6.0Ω	
Turn-On Rise Time (Note 13)	tr		5.8	_	ns		
Turn-Off Delay Time (Note 13)	t <sub>D(off)</sub>	_	55	_	ns		
Turn-Off Fall Time (Note 13)	tf		23	_	ns		

Notes:

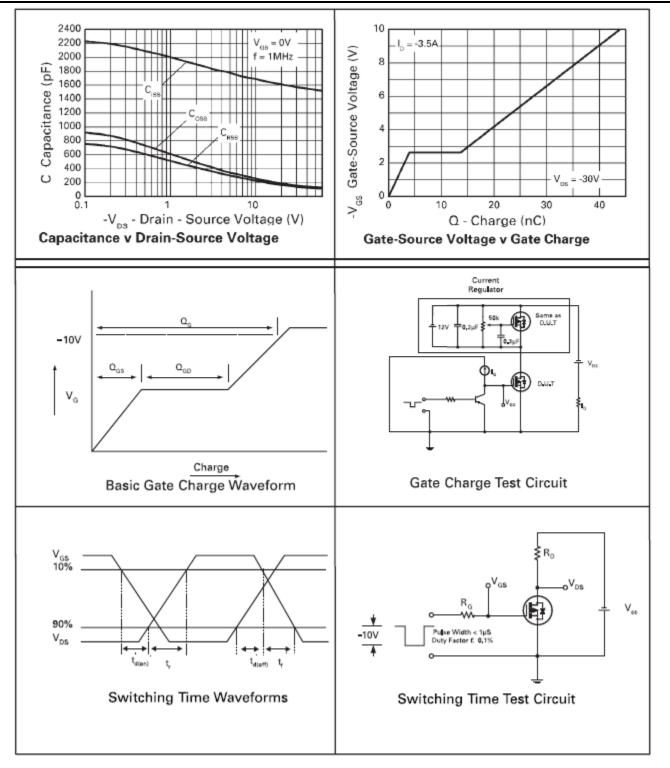


# **Typical Characteristics**





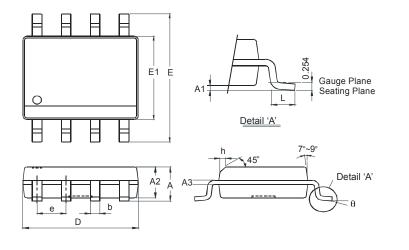
# Typical Characteristics (cont.)





## **Package Outline Dimensions**

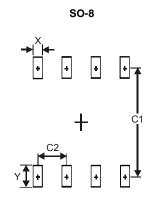
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SO-8					
Dim	Min	Max			
Α	-	1.75			
A1	0.10	0.20			
A2	1.30	1.50			
A3	0.15	0.25			
b	0.3	0.5			
D	4.85	4.95			
ш	5.90	6.10			
E1	3.85 3.95				
e	1.27 Тур				
h	-	0.35			
L	0.62	0.82			
θ	0° 8°				
All Dimensions in mm					

#### **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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